ISOLATED SCRs8 AMPERES RMS

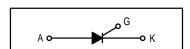
50 thru 800 VOLTS

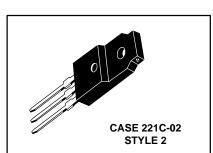
Silicon Controlled Rectifiers

Reverse Blocking Thyristors

... designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 80 A Surge Current Capability
- Insulated Package Simplifies Mounting





MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ (T _J = -40 to +125°C, Gate Open)	VDRM VRRM		Volts
MCR218-2FP MCR218-4FP MCR218-6FP MCR218-8FP MCR218-10FP		50 200 400 600 800	
On-State RMS Current (T _C = +70°C) Full Cycle Sine Wave 50 to 60 Hz ⁽²⁾	I _T (RMS)	8	Amps
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, T _C = +70°C) Preceded and followed by rated current	ITSM	80	Amps
Circuit Fusing (t = 8.3 ms)	I ² t	26	A ² s
Peak Gate Power (T _C = +70°C, Pulse Width = 10 μs)	P _{GM}	5	Watts
Average Gate Power (T _C = +70°C, t = 8.3 ms)	P _G (AV)	0.5	Watt
Peak Gate Current ($T_C = +70^{\circ}C$, Pulse Width = 10 μ s)	I _{GM}	2	Amps
RMS Isolation Voltage (T _A = 25°C, Relative Humidity ≤ 20%)	V _(ISO)	1500	Volts
Operating Junction Temperature	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +125	°C

^{1.} V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



^{2.} The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Forward Blocking Current $(V_D = Rated \ V_{DRM}, \ Gate \ Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	IDRM	_	_	10 2	μA mA
Peak Reverse Blocking Current (V _R = Rated V _{RRM} , T _J = 125°C)	I _{RRM}	_	_	2	mA
Forward "On" Voltage(1) (I _{TM} = 16 A Peak)	VTM	_	1	1.8	Volts
Gate Trigger Current (Continuous dc) (Anode Voltage = 12 Vdc, R _L = 100 Ohms)	lGT	_	10	25	mA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 12 Vdc, R _L = 100 Ohms)	VGT		_	1.5	Volts
Gate Non-Trigger Voltage (Anode Voltage = Rated V _{DRM} , R _L = 100 Ohms, T _J = 125°C)	V _{GD}	0.2	_	_	Volts
Holding Current (Anode Voltage = 12 Vdc)	Ιн	_	16	30	mA
Turn-On Time (I _{TM} = 8 A, I _{GT} = 40 mAdc)	^t gt	_	1.5	_	μs
Turn-Off Time (V_D = Rated V_{DRM} , I_{TM} = 8 A, I_R = 8 A) I_J = 25°C I_J = 125°C	tq	_	15 35	_	μs
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V _D = Rated V _{DRM} , Exponential Waveform)	dv/dt	_	100	_	V/μs

^{1.} Pulse Test: Pulse Width = 1 ms, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

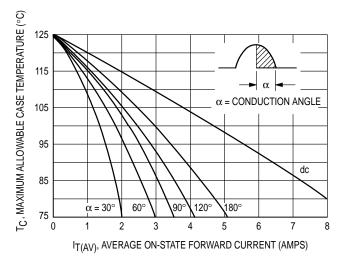


Figure 1. Current Derating

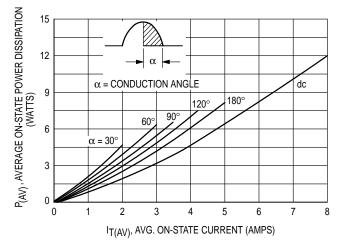
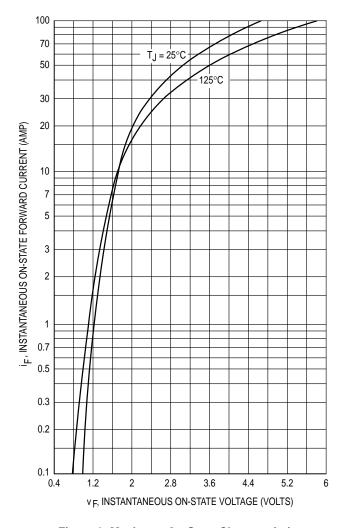


Figure 2. On-State Power Dissipation



80

(GWE)

75

70

70

65

TC = 85°C

f = 60 Hz

SURGE IS PRECEDED AND
FOLLOWED BY RATED CURRENT

1 2 3 4 6 8 10

NUMBER OF CYCLES

Figure 4. Maximum Non-Repetitive Surge Current

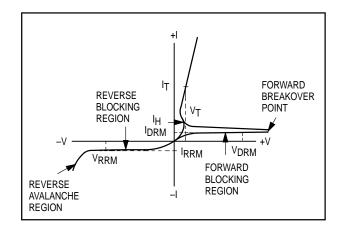


Figure 3. Maximum On-State Characteristics

Figure 5. Characteristics and Symbols

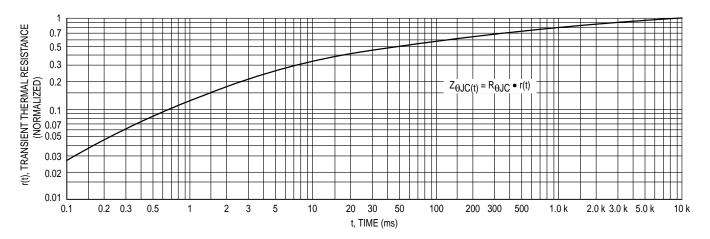


Figure 6. Thermal Response

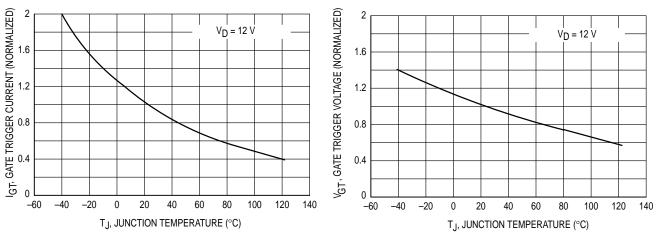


Figure 7. Gate Trigger Current versus Temperature

Figure 8. Gate Trigger Voltage versus Temperature

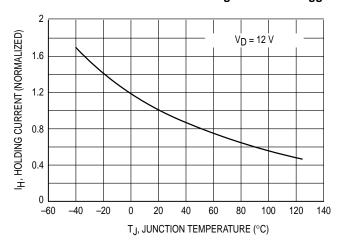
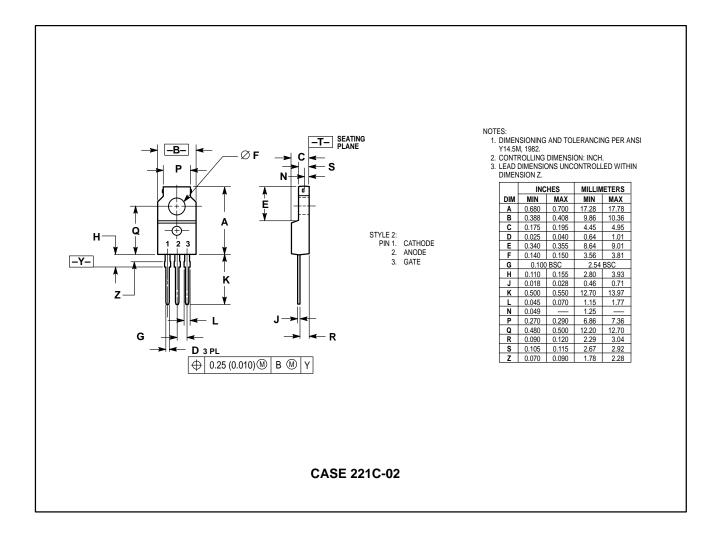


Figure 9. Holding Current versus Temperature

PACKAGE DIMENSIONS



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